Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A dielectric ceramic composition including at least

a main component containing a dielectric oxide having a composition expressed by $[(Ca_xSr_{1-x})O]_m[(Ti_yZr_{1-y-z}Hf_z)O_2]$,

a first subcomponent containing a Mn oxide and/or an Al oxide, and

a glass component containing at least SiO_2 as a primary component:

wherein "m", "x", "y" and "z" indicating composition mole ratios in the formula included in said main component are in relationships of

$0.90 \leq m \leq 1.04$

$0.5 \leq x < 1$

$0.01 \leq y \leq 0.10$

$\cancel{0<z\leq 0.20}$ $\underline{0.5\leq z\leq 0.20}$, and

said dielectric ceramic composition is produced by obtaining a calcinated substance by collectively calcinating at least a main component material, which becomes said main component, a first subcomponent material, which becomes said first subcomponent, and a glass component material, which becomes said glass component, to bring solid phase reaction, and then main firing said calcinated substance.

2. (Original) The dielectric ceramic composition as set forth in claim 1, including 0.2 to 5 mol% of said Mn oxide in terms of MnO and 0.1 to 10 mol% of said Al oxide in terms of Al_2O_3 with respect to 100 mol% of said main component.

3. (Previously Presented) The dielectric ceramic composition as set forth in claim 1, including more than 0 mol% and 2.5 mol% or less of a V oxide in terms of V_2O_5 with respect to 100 mol% of said main component.

4. (Canceled)

5. (Previously Presented) The dielectric ceramic composition as set forth in claim 1, wherein said glass component is expressed by $[(Ba_vCa_{1-v})O]_wSiO_2$, "v" and "w" in the composition formula of said glass component are in ranges of $0 \leq v \leq 1$ and $0.5 \leq w \leq 4.0$, and said glass component is included by 0.5 to 15 mol% with respect to 100 mol% of said main component.

6. (Previously Presented) The dielectric ceramic composition as set forth in claim 1, including at least one of rare earth elements including elements selected from the group consisting of Sc, Y, La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu by 0.02 to 1.5 mol% with respect to 100 mol% of said main component.

7. (Previously Presented) The dielectric ceramic composition as set forth in claim 1, including at least one of Nb, Mo, Ta, W and Mg by 0.02 to 1.5 mol% with respect to 100 mol% of said main component.

8. (Previously Presented) The dielectric ceramic composition as set forth in claim 1, wherein "m" indicating a composition mole ratio in the formula contained in said main component is $1.005 \leq m \leq 1.025$.

9. (Previously Presented) A production method of the dielectric ceramic composition as set forth in claim 1, comprising the steps of:

preparing at least said main component material, said first subcomponent material and said glass component material;

mixing said prepared materials;

obtaining a calcinated substance by collectively calcinating said mixed materials to bring solid-phase reaction by using a dry synthesis method; and

obtaining said dielectric ceramic composition by performing main firing on said calcinated substance.

10. (Previously Presented) An electronic device having a dielectric layer:

wherein said dielectric layer is composed of the dielectric ceramic composition as set forth in claim 1.

11. (Previously Presented) An electronic device having alternately stacked internal electrodes and dielectric layers, wherein said dielectric layers are composed of the dielectric ceramic composition as set forth in claim 1.

12. (Original) The electronic device as set forth in claim 11, wherein said internal electrode includes at least nickel.

13. (Previously Presented) The electronic device as set forth in claim 11, wherein an average particle diameter of a crystal in said dielectric layer is 2 μm or less.

14. (Previously Presented) A production method of the electronic device as set forth in claim 11, comprising the steps of:

preparing at least said main component material, said first subcomponent material and said glass component material;

mixing said prepared materials;

obtaining a calcinated substance by collectively calcinating said mixed materials to bring solid-phase reaction by using a dry synthesis method;

obtaining a green chip comprising by stacking a dielectric paste containing said calcinated substance and internal electrode paste; and

performing main firing on said green chip at 1300°C or lower.